

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (currently amended): A nitride semiconductor substrate comprising:  
a group III nitride semiconductor substrate;  
a mask formed over the group III nitride semiconductor substrate; and  
a group III nitride semiconductor multilayer film formed above the mask,  
wherein the group III nitride semiconductor substrate has a dislocation density in a vicinity of a surface thereof of  $1 \times 10^7/\text{cm}^2$  or less, and  
the mask has a polycrystalline material deposited on a surface thereof,  
wherein a part of the mask is not covered with said semiconductor multilayer film.
2. (original): The nitride semiconductor substrate according to Claim 1, wherein the polycrystalline material is formed from a material containing aluminum and nitrogen as essential elements.
3. (original): The nitride semiconductor substrate according to Claim 1, wherein voids are formed on the surface of the mask having the polycrystalline material.

4. (original): The nitride semiconductor substrate according to Claim 1, wherein the mask is provided on the surface of the group III nitride semiconductor substrate.

5. (canceled).

6. (currently amended): A nitride semiconductor device comprising:  
a group III nitride semiconductor substrate;  
a mask formed over the group III nitride semiconductor substrate; and  
a group III nitride semiconductor multilayer film formed above the mask, the group III nitride semiconductor multilayer film including an active layer,  
wherein the group III nitride semiconductor substrate has a dislocation density in a vicinity of a surface thereof of  $1 \times 10^7/\text{cm}^2$  or less, and  
the mask has a polycrystalline material deposited on a surface thereof,  
wherein a part of the mask is not covered with said semiconductor multilayer film.

7. (original): The nitride semiconductor device according to Claim 6, wherein the polycrystalline material is formed from a material containing aluminum and nitrogen as essential elements.

8. (original): The nitride semiconductor device according to Claim 6, wherein voids are formed on the surface of the mask having the polycrystalline material.

9. (original): The nitride semiconductor device according to Claim 6, wherein the mask is provided on the surface of the group III nitride semiconductor substrate.

10. (canceled).

11. (previously presented): The nitride semiconductor device according to Claim 6, wherein the mask is provided in a vicinity of a device separating groove of the nitride semiconductor device.

12-21. (canceled).

22. (new): A nitride semiconductor substrate comprising:  
a group III nitride semiconductor substrate;  
a mask formed over the group III nitride semiconductor substrate; and  
a group III nitride semiconductor multilayer film formed above the mask,  
wherein the group III nitride semiconductor substrate has a dislocation density in a vicinity of a surface thereof of  $1 \times 10^7/\text{cm}^2$  or less, and  
the mask has a polycrystalline material deposited on a surface thereof,  
wherein said semiconductor multilayer film has a dislocation density directly on the mask of  $1 \times 10^7/\text{cm}^2$  or less.

23. (new): The nitride semiconductor device according to Claim 22, wherein the group III nitride semiconductor multilayer film formed above the mask has flat interfaces.

24. (new): A nitride semiconductor device comprising:  
a group III nitride semiconductor substrate;  
a mask formed over the group III nitride semiconductor substrate; and  
a group III nitride semiconductor multilayer film formed above the mask, the group III nitride semiconductor multilayer film including an active layer,  
wherein the group III nitride semiconductor substrate has a dislocation density in a vicinity of a surface thereof of  $1 \times 10^7/\text{cm}^2$  or less, and  
the mask has a polycrystalline material deposited on a surface thereof,  
wherein said semiconductor multilayer film has a dislocation density directly on the mask of  $1 \times 10^7/\text{cm}^2$  or less.

25. (new): The nitride semiconductor device according to Claim 24, wherein the group III nitride semiconductor multilayer film formed above the mask has flat interfaces.